

EAST - [10785310 trench\NROM.wsp:1]

FileViewEditToolsWindowHelp

Active

L1: (1158301) (nrom read adj only adj memory)

L2: (11) 10/785310

L3: (231318) (sonos monos minos nrom nitride adj3 memory)

L4: (771) (nrom)

L5: (1998) ((nonvolatile non adj volatile) adj read adj only)

L6: (71) 4 with 5

L7: (832) (nrom nitride adj read adj only adj memory)

L8: (1391) (nitride adj read adj only adj memory)

L9: (1392) (nitride adj read adj only)

L10: (322) 8 with 4

L11: (88825) trench\$3

L12: (833) 8 4

L13: (32) 11 with 12

L14: (46) 11 same 12

L15: (785282) (select\$4 side control) adj (gate line) \$6

L16: (171) 14 and 15

L17: (168) 11 and 12

L18: (684496) (select\$4 side 1 adj (gate line) \$6

L19: (68) 17 and 18

L20: (1251684) group\$3

L21: (21) 12 with 20

L22: (21) 12 same 20

L23: (553) nor adj memory

L24: (4) 23 with 11

L25: (15) 23 same 11

US: US PLATE L20NT, L20NT, L20NT, L20NT, L20NT, L20NT

Device group: UN

23 same 11

April 2005

US 200500 2005 3 Fabrication of conductive gates for non 438/25 438/268

US 200402 2004 3 Fabrication of dielectric on a gate surf 438/58 438/197

US 200402 2004 3 FABRICATION OF GATE DIELECTRIC IN NORW 438/25

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US 200302 2003 2 Nor flash memory cell with high storag 365/18

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US 20050

US 20040

US 20040

US 20040

US 20040

US 20040

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US 20040

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US 20020

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